



20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C		
	9mΩ @ V _{GS} = -4.5V	-13A		
-20V	11mΩ @ V _{GS} = -2.5V	-12A		
	16mΩ @ V _{GS} = -1.8V	-10A		

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

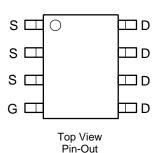
- Load Switch
- Power Management Functions

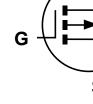
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)



Top View





Equivalent Circuit

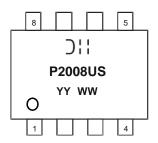
Ordering Information (Note 4)

- 1			
	Part Number	Case	Packaging
	DMP2008USS-13	SO-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



J;; = Manufacturer's Marking
P2008US = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 20 = 2020)
WW = Week (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-20	V		
Gate-Source Voltage			Vgss	±8	V
Continuous Drain Current (Note 6) Vgs = -4.5V	lo	-13 -10 -38	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	I _{DM}	-110	Α		
Pulsed Body Diode Forward Current (380µs Pulse	I _{SM}	-110	Α		
Maximum Continuous Body Diode Forward Curren	Is	-49	Α		
Avalanche Current (Note 7)			las	-119	Α
Avalanche Energy (Note 7)	E _{AS}	110	mJ		

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{OJA}	87	°C/W
Total Power Dissipation (Note 6)	Steady State	PD	2.3	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		Rөja	54	°C/W
Thermal Resistance, Junction to Case (Note 6)		Rejc	7	*C/VV
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

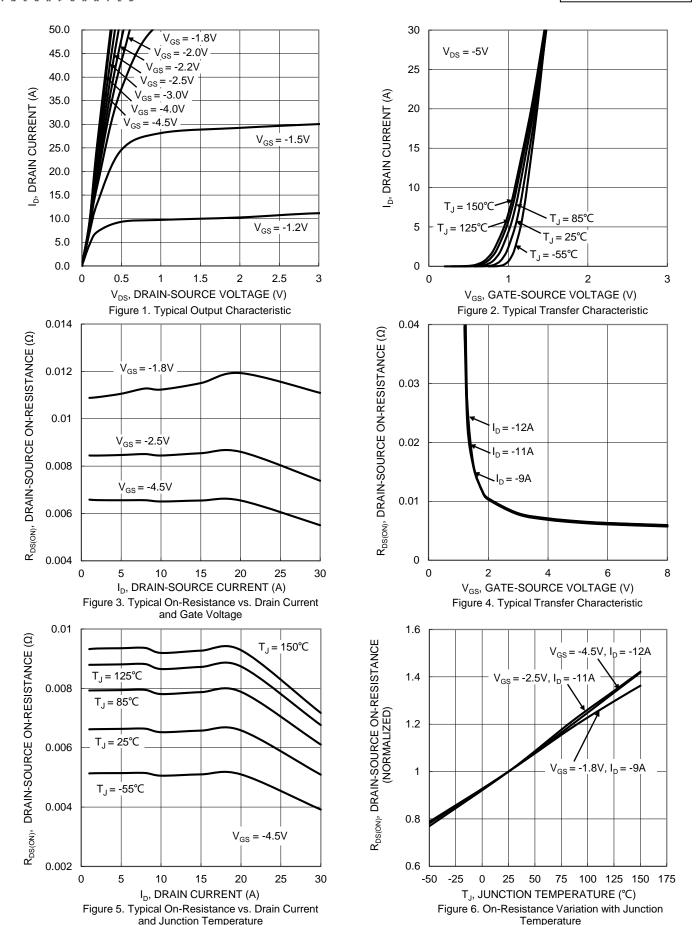
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	-20	_	_	V	V _G S = 0V, I _D = -250μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -16V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(TH)	-0.4	_	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
		_	6.5	9		$V_{GS} = -4.5V$, $I_{D} = -12A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	8.4	11	mΩ	$V_{GS} = -2.5V$, $I_{D} = -11A$	
		_	11.2	16		$V_{GS} = -1.8V, I_{D} = -9A$	
Diode Forward Voltage	VsD	_	-0.7	-1.2	V	V _G S = 0V, I _S = -10A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	6820	_		V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss	_	622	_	pF		
Reverse Transfer Capacitance	Crss	_	589	_			
Gate Resistance	Rg	_	2.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	76	_		V _{DS} = -10V, I _D = -12A	
Total Gate Charge (V _{GS} = -10V)	Qg	_	159	_	nC		
Gate-Source Charge	Qgs	_	6.9	_	nC nC		
Gate-Drain Charge	Qgd	_	15.6	_			
Turn-On Delay Time	t _{D(ON)}	_	22	_		$V_{GS} = -4.5V$, $V_{DS} = -10V$, $R_{G} = 6\Omega$, $I_{D} = -12A$	
Turn-On Rise Time	t _R	_	33	_			
Turn-Off Delay Time	tD(OFF)	_	291	_	ns		
Turn-Off Fall Time	t _F	_	124	_			
Reverse Recovery Time	trr	_	25	_	ns	I _F = -12A, di/dt = 100A/μs	
Reverse Recovery Charge	Q _{RR}		16	_	nC	I _F = -12A, di/dt = 100A/µs	

5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate. Notes:

- 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

2 of 7 DMP2008USS January 2020 © Diodes Incorporated Document number: DS41287 Rev. 3 - 2







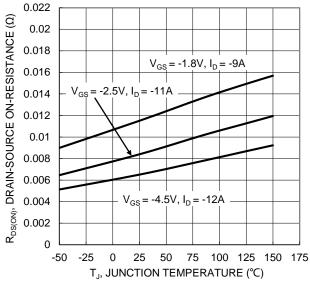


Figure 7. On-Resistance Variation with Junction Temperature

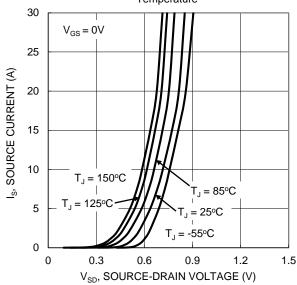
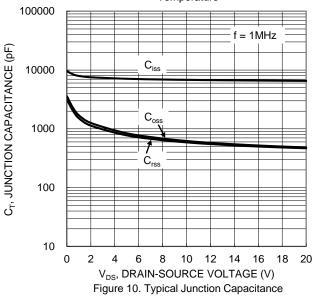
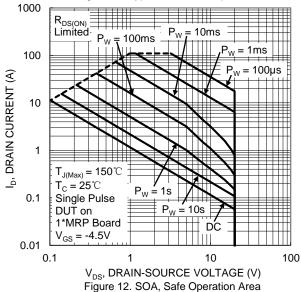


Figure 9. Diode Forward Voltage vs. Current 10 8 6 $V_{GS}(V)$ 4 $V_{DS} = -10V, I_{D} = -12A$ 2 0 0 25 50 75 100 125 150 175 Q_g (nC) Figure 11. Gate Charge

Figure 8. Gate Threshold Variation vs. Junction Temperature







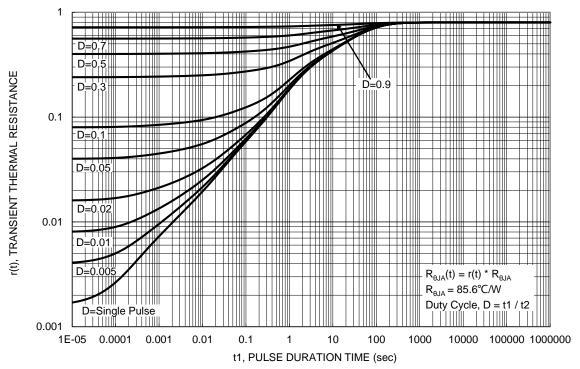


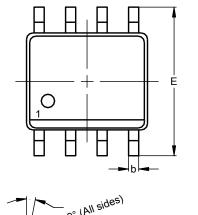
Figure 13. Transient Thermal Resistance

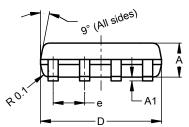


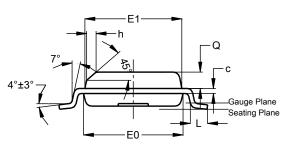
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





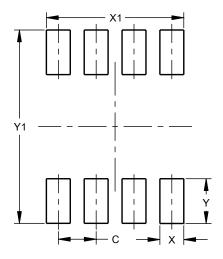


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
C	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h			0.35		
١	0.62	0.82	0.72		
ø	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Y	1.505			
V4	C EO			



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7 of 7 DMP2008USS Document number: DS41287 Rev. 3 - 2

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